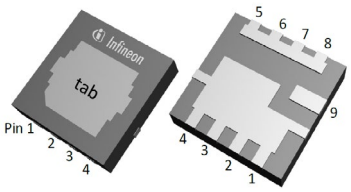
英飞凌MOSFET

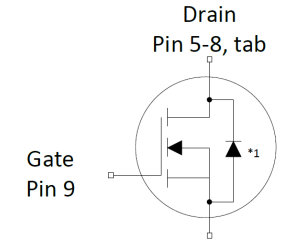
PG-WHTFN-9 (3x3)

英飞凌OptiMOS™ 6 功率晶体管，80 V



特性

- 针对高性能 SMPS 进行了优化
- N沟道，逻辑电平
- 极低的导通电阻 $R_{DS(on)}$
- 卓越的热阻
- 100% 雪崩测试
- 工作温度 175°C
- 无铅镀层；符合 RoHS 标准
- 符合 IEC61249-2-21 标准的无卤素



*1: Internal body diode

产品验证

符合 JEDEC JESD47, JESD22 和 J-STD-020 相关测试的工业应用要求。

表 1　　主要性能参数

Parameter	Value	Unit
V_{DS}	80	V
$R_{DS(on),max}$ V_{GS}=10 V	3.15	mΩ
$R_{DS(on),max}$ V_{GS}=4.5 V	4.0	mΩ
I_D	127	A
Q_{oss}	57	nC
Q_G(0V…4.5V)	33	nC
Q_{rr}(100A/µs)	20	nC

Part number	Package	Marking	Related links
IQE031N08LM6CGSC	PG-WHTFN-9	N	-

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1 最大额定值

除非另有规定，T_A =25 °C

表 2 最大额定值

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current [1]	I_D	-	-	127	A	V_{GS}=10 V, T_C=25 °C
				90		V_{GS}=10 V, T_C=100 °C
				80		V_{GS}=4.5 V, T_C=100 °C
				18		V_{GS}=10 V, T_A=25 °C, R_{THJA}=60 °C/W [2]
Pulsed drain current [3]	$I_{D,pulse}$	-	-	508	A	T_C=25 °C
Avalanche energy, single pulse [4]	E_{AS}	-	-	203	mJ	I_D=20 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	125	W	T_C=25 °C
				2.5		T_A=25 °C, R_{thJA}=60 °C/W [2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

1) 额定值指产品仅具有数据手册指定的绝对最大值，保持外壳温度符合规定要求。其他外壳温度请参见图 2。需要根据实际环境条件降低额定值。

2) 器件置于40 mm × 40 mm × 1.5 mm 环氧树脂 PCB FR4 上，配有6 cm^2（单层，70 µm厚）铜层面积用于漏极连接。PCB在静止空气中垂直放置。

3) 详细信息请参见图 3.

4) 详细信息请参见图 13.

2 热特性

表 3 热特性

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.2	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}		0.7	1.4		
Thermal resistance, junction - ambient, 6 cm^2 cooling area [5)]	R_{thJA}		-	60		

5) 器件置于40 mm × 40 mm × 1.5 mm 环氧树脂 PCB FR4 上，配有6 cm^2（单层，70 µm厚）铜层面积用于漏极连接。PCB在静止空气中垂直放置。

3 电气特性

除非另有规定，T_j = 25°C

表 4 静态特性

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	80	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	1.1	1.7	2.3	V	V_{DS}=V_{GS}, I_D=50.8 µA
Zero gate voltage drain current	I_{DSS}	-	0.1	1	µA	V_{DS}=64 V, V_{GS}=0 V, T_j=25 °C
			10	100		V_{DS}=64 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	2.80	3.15	mΩ	V_{GS}=10 V, I_D=20 A
			3.36	4.0		V_{GS}=4.5 V, I_D=10 A
Gate resistance	R_G	0.3	0.55	0.8	Ω	-
Transconductance [6]	g_{fs}	55	110	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=20 A

[6] 由设计指定，未经过生产测试。

表 5 动态特性

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance [7]	C_{iss}	-	3500	4600	pF	V_{GS}=0 V, V_{DS}=40 V, f=1 MHz
Output capacitance [7]	C_{oss}		660	860		
Reverse transfer capacitance [7]	C_{rss}		35	61		
Turn-on delay time	$t_{d(on)}$	-	17	-	ns	V_{DD}=40 V, V_{GS}=4.5 V, I_D=10 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r		17			
Turn-off delay time	$t_{d(off)}$		21			
Fall time	t_f		9.3			

[7] 由设计指定，未经过生产测试。

表 6　　栅极电荷特性 [8)]

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	9.1	-	nC	V_{DD}=40 V, I_D=10 A, V_{GS}=0 to 4.5 V
Gate charge at threshold	$Q_{g(th)}$		5.9	-	nC	
Gate to drain charge [9)]	Q_{gd}		7.9	12	nC	
Switching charge	Q_{sw}		11	-	nC	
Gate charge total [9)]	Q_g		26	33	nC	
Gate plateau voltage	$V_{plateau}$		2.6	-	V	
Gate charge total [9)]	Q_g	-	54	68	nC	V_{DD}=40 V, I_D=10 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	22	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 4.5 V
Output charge [9)]	Q_{oss}	-	57	74	nC	V_{DS}=40 V, V_{GS}=0 V

[8)] 参数定义请参数见“栅极充电波形”。

[9)] 由设计定义。未经过生产测试。

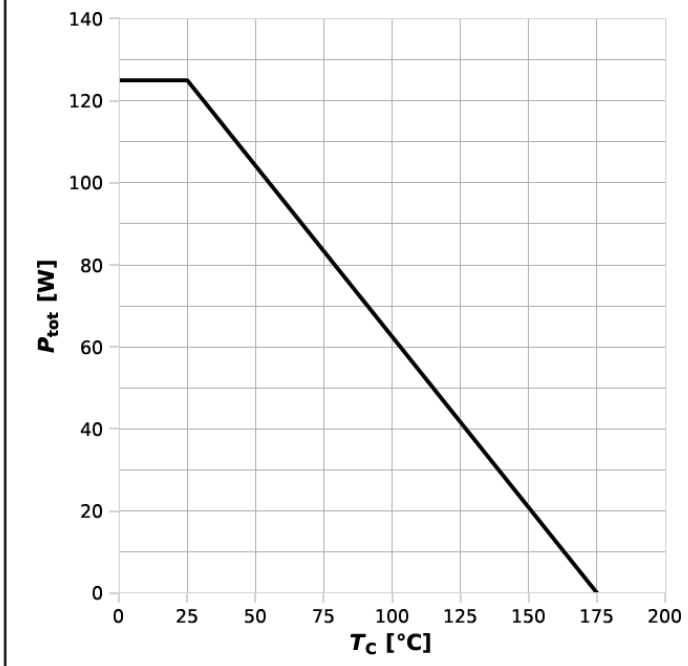
表 7　　反向二极管

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	116	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$			508		
Diode forward voltage	V_{SD}	-	0.79	1.0	V	V_{GS}=0 V, I_F=20 A, T_j=25 °C
Reverse recovery time [10)]	t_{rr}	-	27	54	ns	V_R=40 V, I_F=10 A, di_F/dt=100 A/µs
Reverse recovery charge [10)]	Q_{rr}		20	40	nC	
Reverse recovery time [10)]	t_{rr}	-	18	36	ns	V_R=40 V, I_F=10 A, di_F/dt=1000 A/µs
Reverse recovery charge [10)]	Q_{rr}		115	230	nC	

[10)] 由设计指定，未经过生产测试。

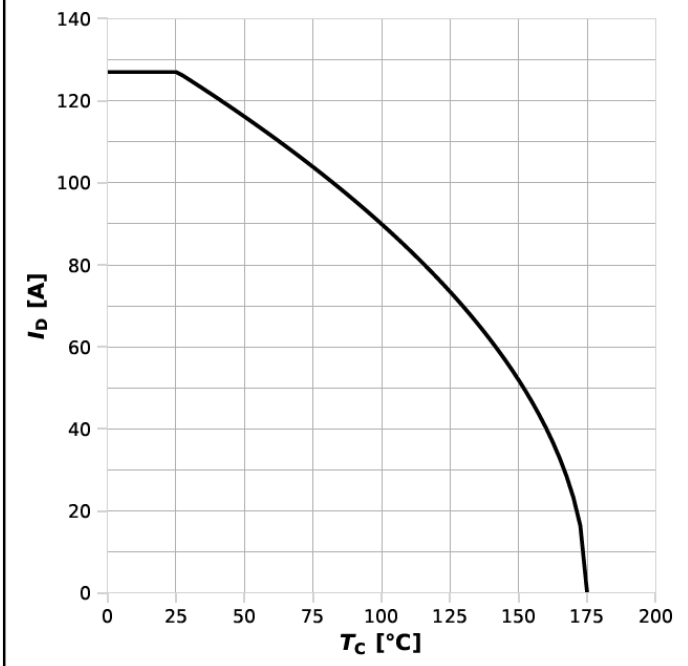
4 电气特性图

Diagram 1: Power dissipation



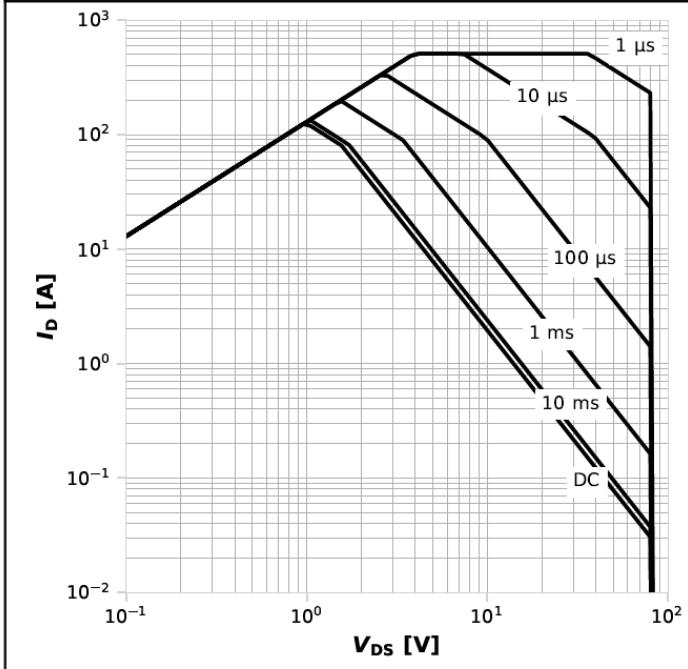
P_{tot}=f(T_C)

Diagram 2: Drain current



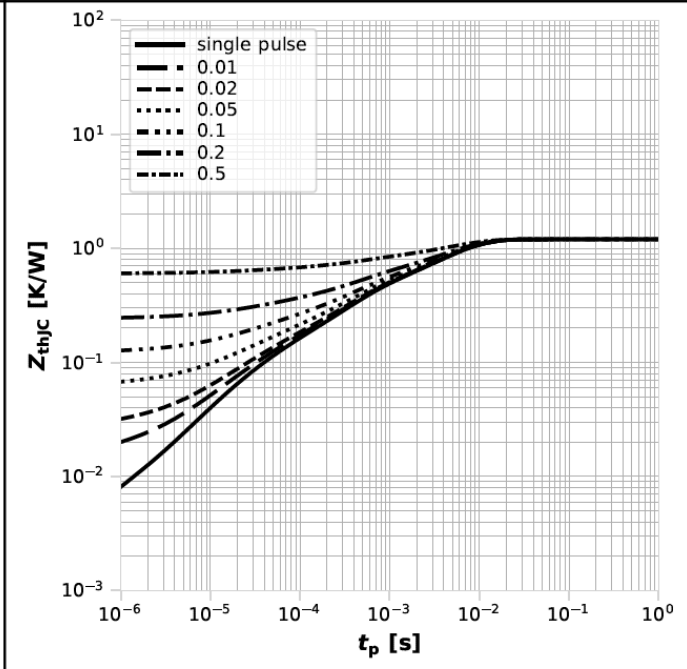
I_D=f(T_C); V_{GS}≥10 V

Diagram 3: Safe operating area



I_D=f(V_{DS}); T_C=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



Z_{thJC}=f(t_p); parameter: D=t_p/T

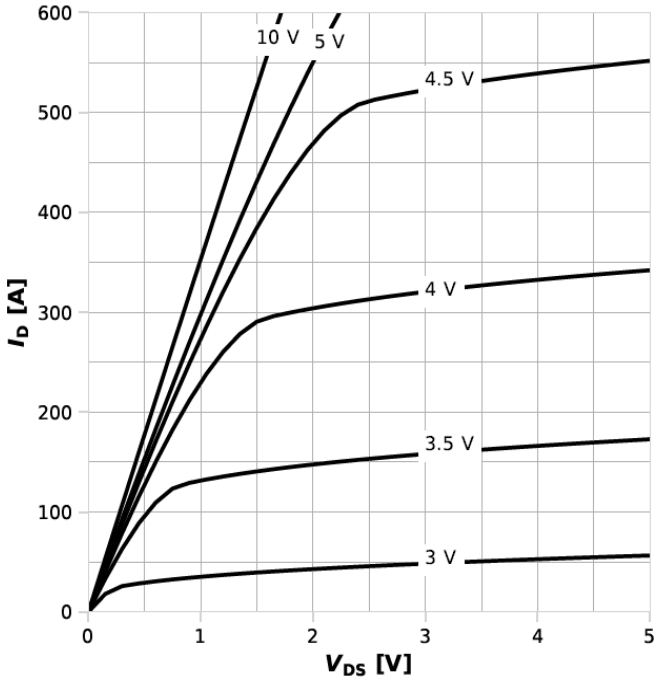
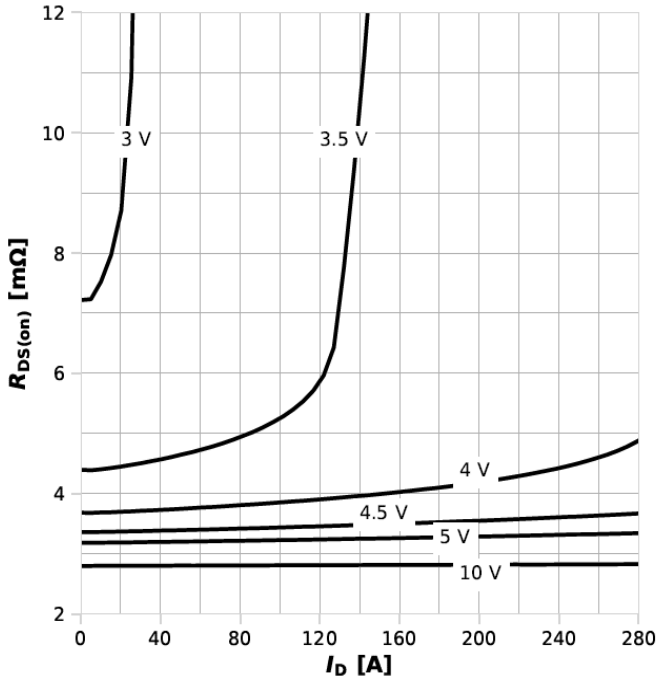
Diagram 5: Typ. output characteristics	Diagram 6: Typ. drain-source on resistance
	
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

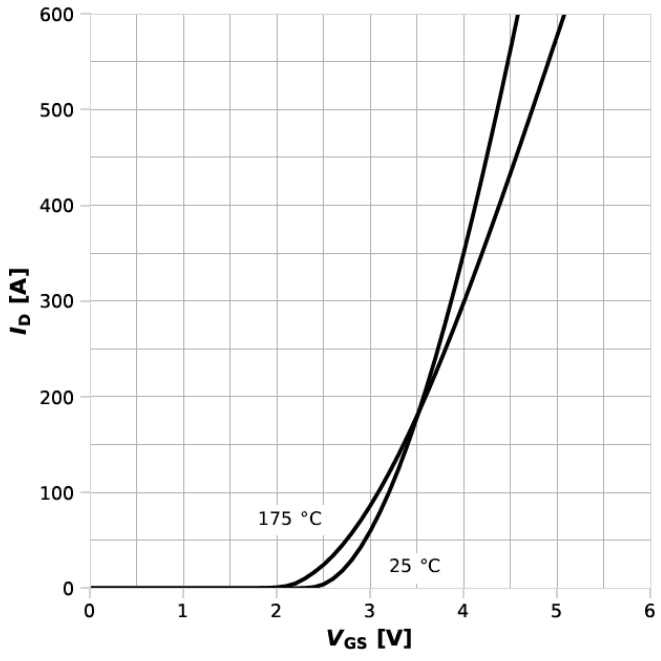
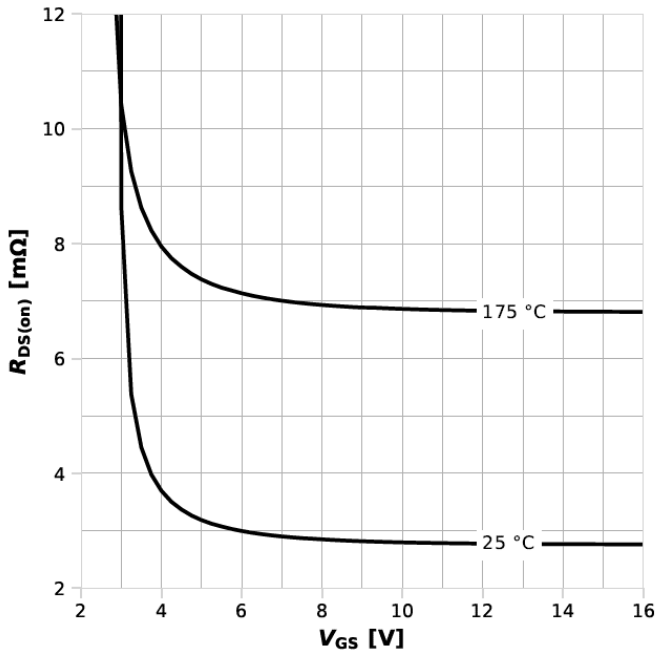
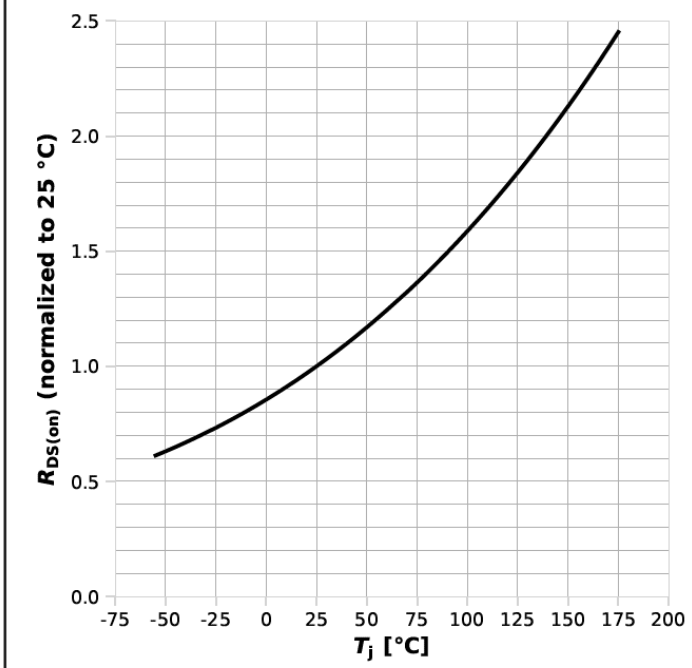
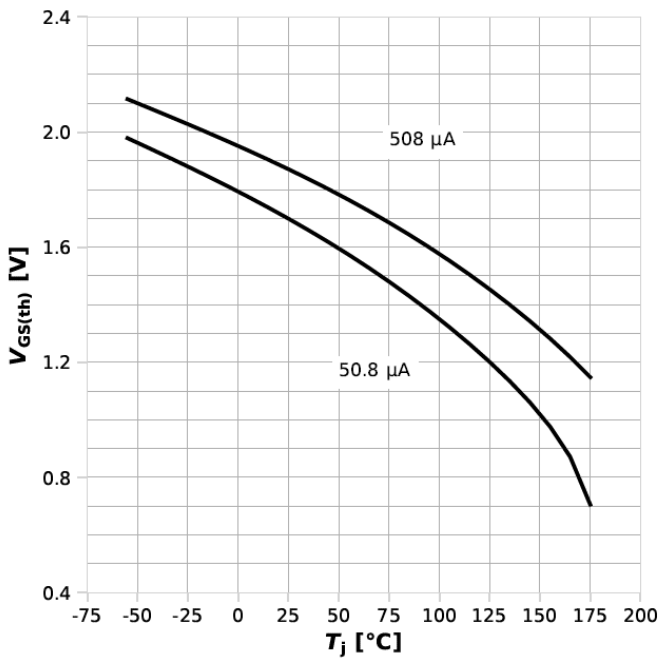
Diagram 7: Typ. transfer characteristics	Diagram 8: Typ. drain-source on resistance
	
I_D=f(V_{GS}), |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j	$R_{DS(on)}$=f(V_{GS}), I_D=20 A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



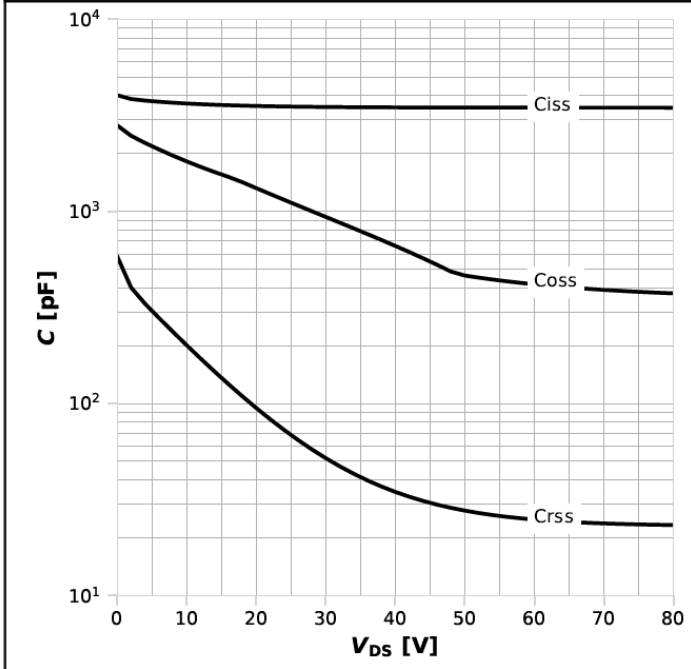
$R_{DS(on)}$=f(T_j), I_D=20 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



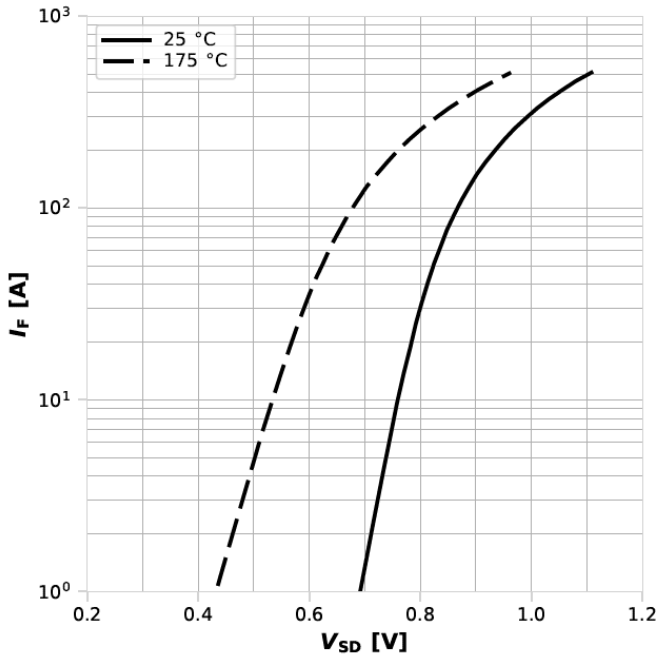
$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

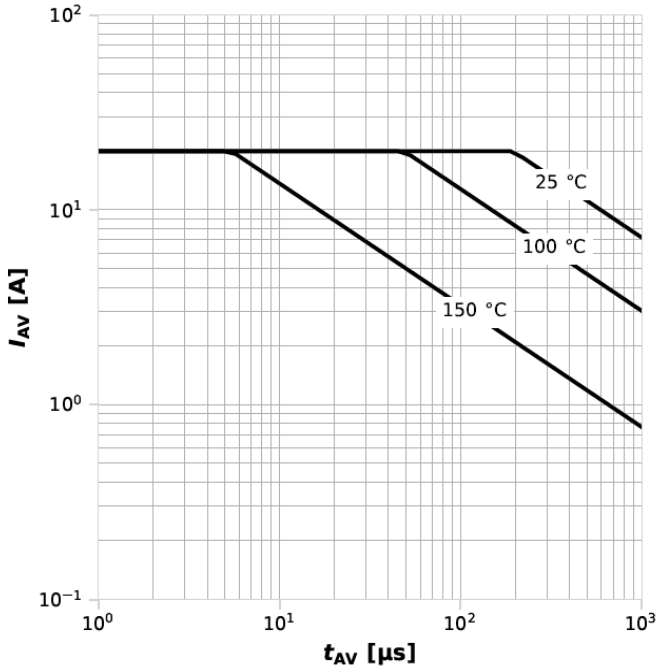
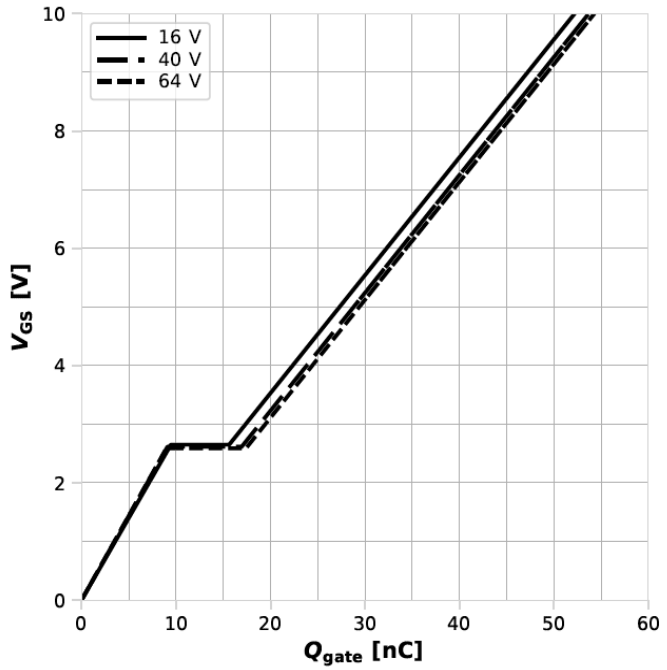
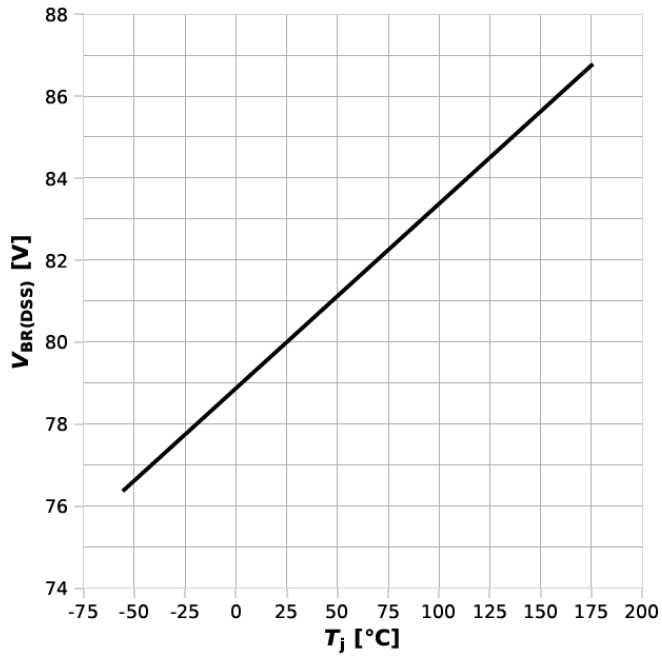
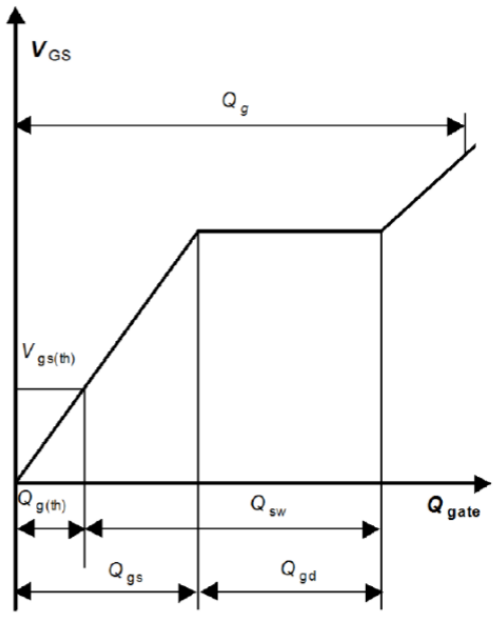
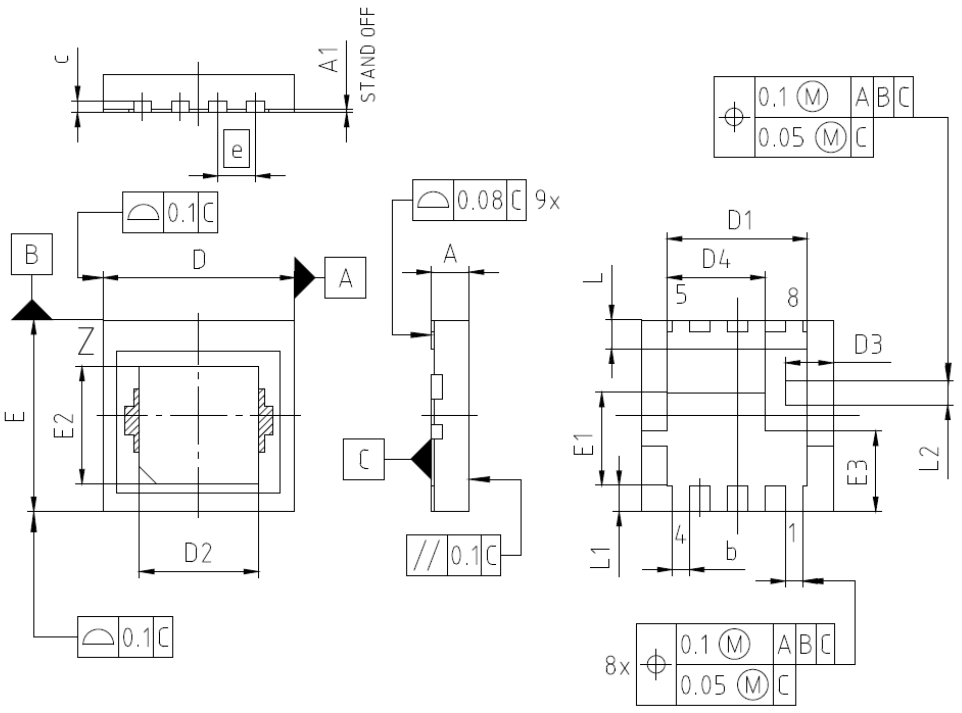
Diagram 13: Avalanche characteristics	Diagram 14: Typ. gate charge
	
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$	V_{GS}=f(Q_{gate}), I_D=10 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Min. drain-source breakdown voltage	Gate charge waveforms
	
$V_{BR(DSS)}$=f(T_j); I_D=1 mA	-

5 封装外形



PACKAGE - GROUP NUMBER:	PG-WHTFN-9-U01	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.55	0.75
A1	0	0.05
b	0.20	0.40
c	0.10	0.30
D	3.20	3.40
D1	2.31	2.51
D2	1.95	2.25
D3	0.73	0.93
D4	1.58	1.78
E	3.20	3.40
E1	1.50	1.70
E2	1.93	2.23
E3	1.285	1.485
e	0.65	
L	0.40	0.60
L1	0.35	0.55
L2	0.32	0.52

图 1　　PG- WHTFN- 9 封装外形，尺寸单位为毫米

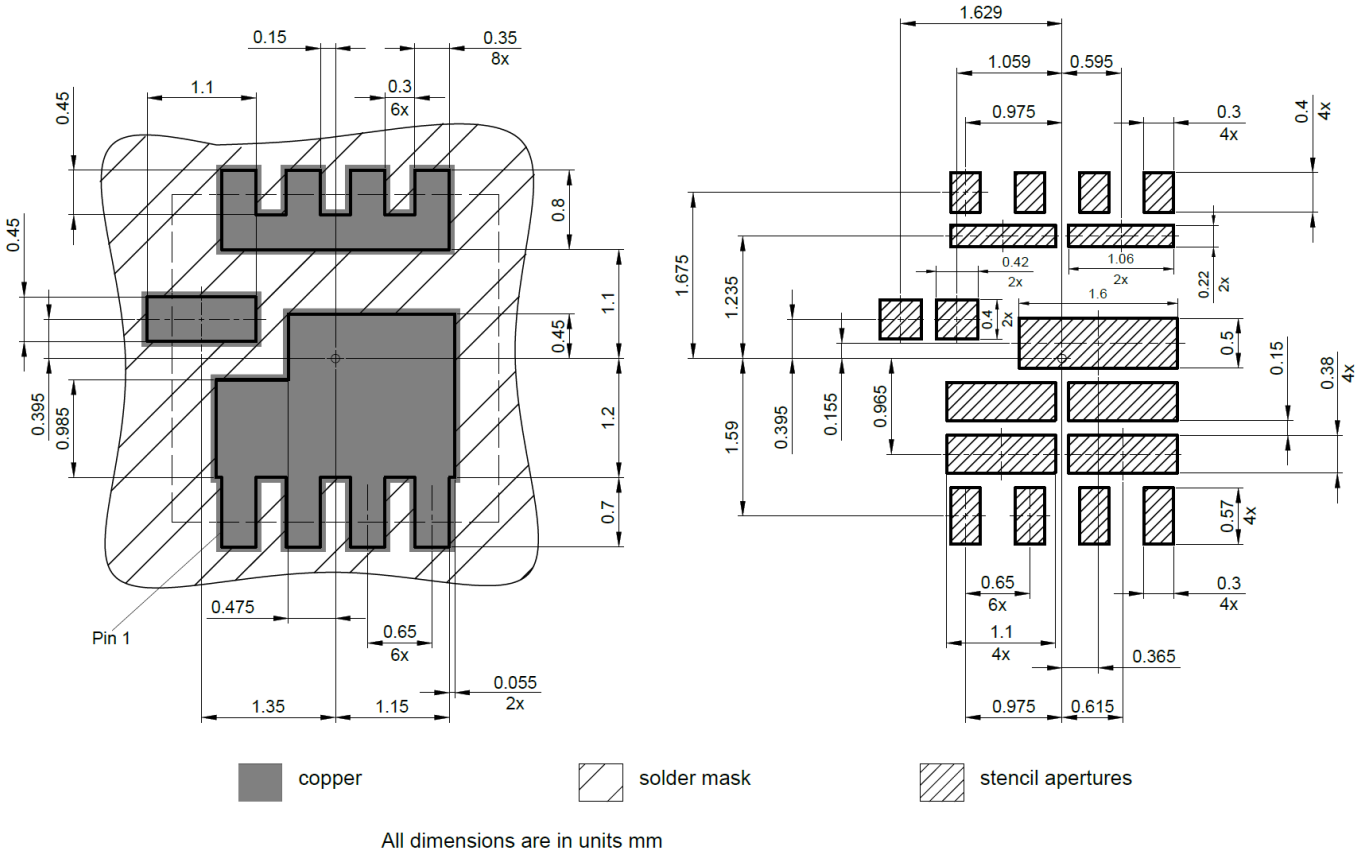


图 2　　PG- WHTFN- 9封装图，尺寸单位为毫米

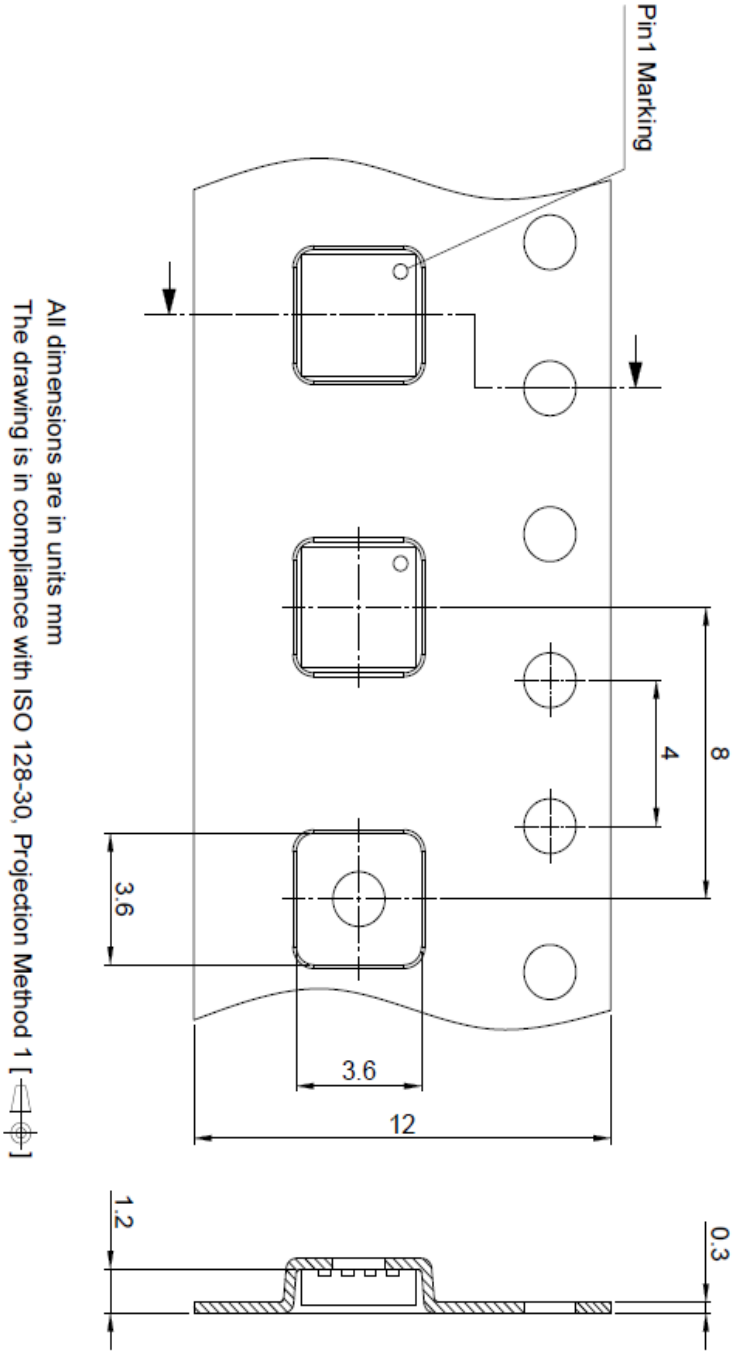


图 3　　PG- WHTFN- 9封装变体，尺寸单位为毫米

修订记录

IQE031N08LM6CGSC

Revision 2025 - 05 - 21 , Rev. 1 . 0

Previous revisions

Revision	Date	Subjects (major changes since last revision)
1.0	2025-05-21	Release of final version

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